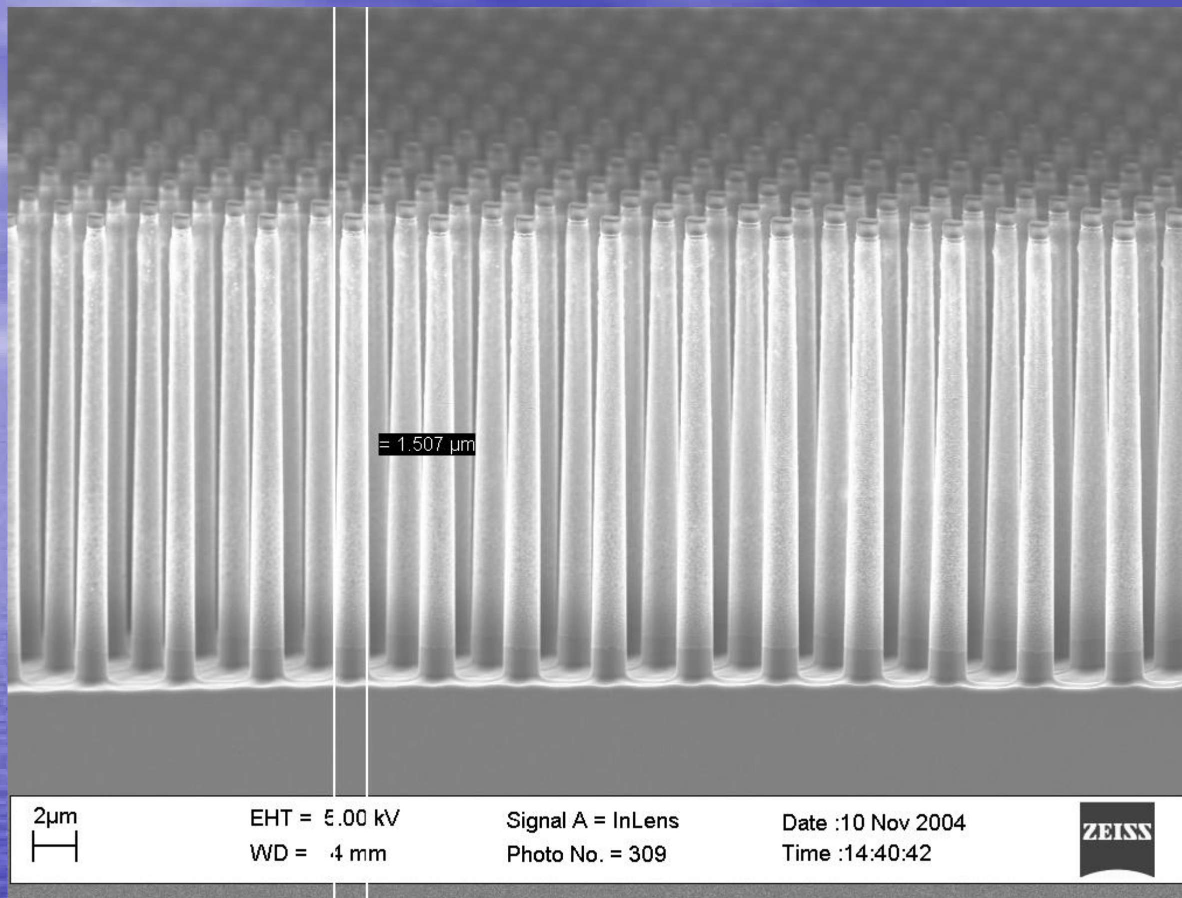
Oxford Plasmalab System 100 ICP-RIE

- 13.56 MHz driven parallel plate reactor
- cooled substrate electrodes
- shower head gas inlet optimized for RIE
- high conductance vacuum layout
- PC 2000 Control
- manual vacuum loadlock
- wide temperature range substrate electrode: -150° C - +400° C, RF driven
- Gases: Cl_2, $SiCl_4$, BCl_3, SF_6, Ar, O_2, H_2 and N_2



- Silicon etching with Cr mask
- 20min with P_{ICP}=500W P_{RIE}=3W, 40sccm SF_6 and 6sccm O_2, Pressure 10mTorr and Temperature -110°C
- SEM micrograph by Grigoras Kestutis (MEC/HUT)